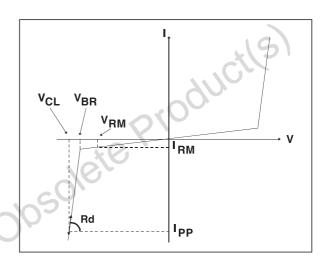
ESDA25DB3

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25°C)

Symbol	Parameter	Value	Unit
V _{PP}	Electrostatic discharge MIL STD 883C - Method 3015-6	25	kV
P _{PP}	Peak pulse power (8/20μs)	500	W
T _{stg}	Storage temperature range Maximum junction temperature	- 55 to + 150 125	ပို့
TL	Maximum lead temperature for soldering during 10s	260	°C

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter					
V_{RM}	Stand-off voltage					
V_{BR}	Breakdown voltage					
V _{CL}	Clamping voltage					
I _{RM}	Leakage current					
I _{PP}	Peak pulse current					
αΤ	Voltage temperature coefficient					
С	Capacitance					



Types	404	BR @	I _R	I _{RM} @	V _{RM}	Rd	αΤ	С
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	min.	max.		max.		typ.	max.	typ.
10,6	note1			note1		note 2	note 3	0V bias
	V	V	mA	μΑ	V	Ω	10 ⁻⁴ /°C	pF
ESDA25DB3	25	30	1	2	24	0.5	9.7	50

 $\begin{array}{l} \textbf{note 1}: \mbox{Betwenn any I/O pin Groung} \\ \textbf{note 2}: \mbox{Square pulse, Ipp} = 25\mbox{A, tp=2.5}\mu\mbox{s}. \\ \textbf{note 3}: \ \Delta \ \mbox{V}_{BR} = \alpha\mbox{T}^* \ (\mbox{Tamb -}25^\circ\mbox{C}) \ ^*\mbox{V}_{BR} \ (25^\circ\mbox{C}) \end{array}$

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CALCULATION OF THE CLAMPING VOLTAGE

USE OF THE DYNAMIC RESISTANCE

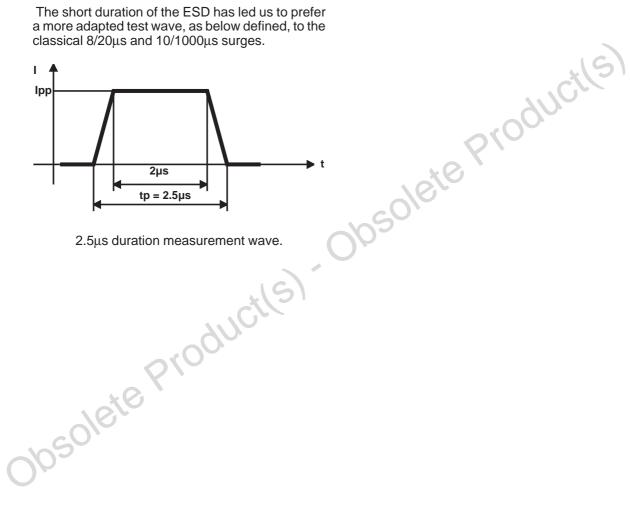
The ESDA family has been designed to clamp fast spikes like ESD. Generally the PCB designers need to calculate easily the clamping voltage V_{CL} . This is why we give the dynamic resistance in addition to the classical parameters. The voltage across the protection cell can be calculated with the following formula:

$$V_{CL} = V_{BR} + RdI_{PP}$$

Where Ipp is the peak current through the ESDA cell.

DYNAMIC RESISTANCE MEASUREMENT

The short duration of the ESD has led us to prefer a more adapted test wave, as below defined, to the



As the value of the dynamic resistance remains stable for a surge duration lower than 20µs, the 2.5µs rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

Fig. 1: Peak power dissipation versus initial junction tempearature.

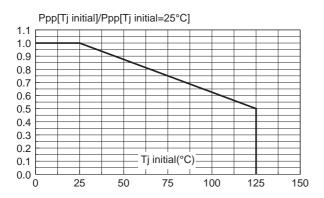


Fig. 2: Peak pulse power versus exponential pulse duration (Tj initial = 25 °C).

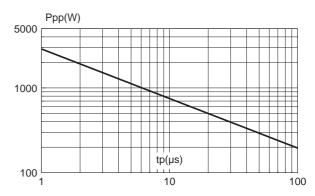


Fig. 3 : Clamping voltage versus peak pulse current (Tj initial = $25 \, ^{\circ}\text{C}$).

Rectangular waveform tp = $2.5 \mu s$.

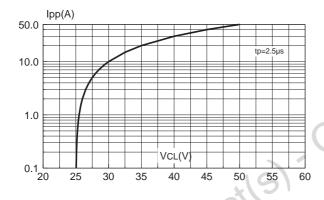


Fig. 4: Capacitance versus reverse applied voltage (typical values).

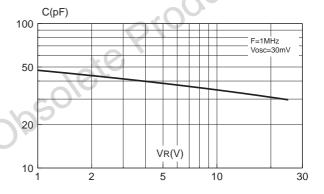
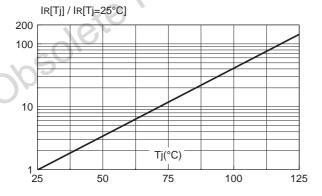
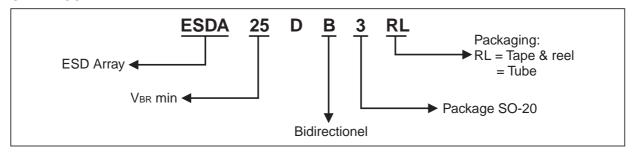


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).



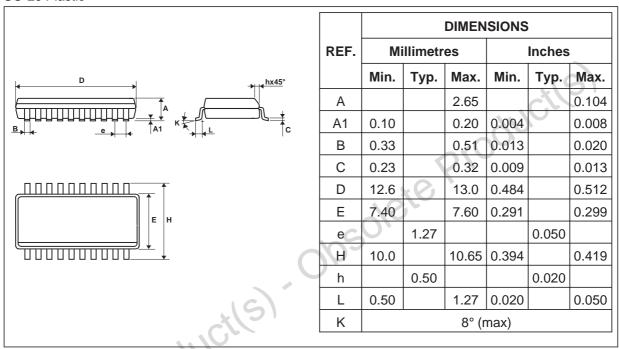
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ORDER CODE



PACKAGE MECHANICAL DATA

SO-20 Plastic



Marking: Logo, Date Code, E25DB3

Packaging: Preferred packaging is tape and reel.

Weight: 0.55g.

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